

AMENDMENTS TO THE SPECIFICATION:

Page 2, replace the paragraph, beginning on line 1, with the following amended paragraph:

--More specifically, a semiconductor chip 1a and a semiconductor chip 1b with a size smaller than the semiconductor chip 1a are laminated by Ag paste 13 on an interposer 12.--

Page 3, replace the paragraph, beginning on line 6, with the following amended paragraph:

--After these semiconductor devices 1 and 3 are laminated and equipped with a desired number, a reflow process is entirely carried out to connect electrodes. Herein, it should be noted that the reference numeral 16 represents flux.--

Page 3, replace the paragraph, beginning on line 24, with the following amended paragraph:

--As illustrated in ~~Fig. 3~~ Fig. 3A, semiconductor chips 1 each having a circuit surface 6 and a back surface 7 are positioned, and are bonded with solder 4. Then, a semiconductor chip 1 to be subsequently laminated is positioned to thereby to bond with the solder.--

Page 8, replace the paragraph, beginning on line 5, with the following amended paragraph:

--As illustrated in Fig. 4, bumps 3 are formed on a circuit surface 6 and a back surface 7 of a semiconductor chip 1, and solder 4 is supplied on the bump 3. Herein, it should be

noted that the reference numeral 2 indicates a penetration electrode.--

Page 8, replace the paragraph, beginning on line 14, with the following amended paragraph:

--The similar process is carried out for the semiconductor chip 1 to be laminated. Further, positioning is conducted in the reduction atmosphere such that the surface of the semiconductor chip 1 activated for the surface is not contaminated again as needed (step 202). Thereafter, ~~heating~~ pressing is carried out (step 203).--

Page 11, replace the paragraph, beginning on line 12, with the following amended paragraph:

--The bumps 3 on the circuit surface ~~[[3]]~~ 6 is formed by gold while the bump 3 on the back surface 7 is formed by copper.--